

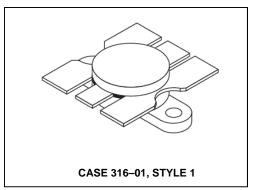
# The RF Line NPN Silicon Power Transistor 60W, 225 to 400MHz, 28V

M/A-COM Products Released - Rev. 07.07

Designed primarily for wideband large-signal output amplifier stages in the 225 to 400 MHz frequency range.

- Guaranteed performance in 225 to 400 MHz broadband amplifier @ 28 Vdc
   Output power = 60 W over 225 to 400 MHz band
   Minimum gain = 7.8 dB @ 400 MHz
- Built-in matching network for broadband operation using double match technique
- 100% tested for load mismatch at all phase angles with 30:1 VSWR
- Gold metallization system for high reliability applications

### **Product Image**



#### MAXIMUM RATINGS\*

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	33	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter–Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Total Device Dissipation @ T <sub>C</sub> = 25°C (1) Derate above 25°C	PD	146 0.83	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +200	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>eJC</sub>	1.2	°C/W

### ELECTRICAL CHARACTERISTICS\* (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	33	_	_	Vdc
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 50 mAdc, V <sub>BE</sub> = 0)	V <sub>(BR)CES</sub>	60	_	_	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 5.0 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	4.0	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	_	2.0	mAdc

NOTE: (continued)

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These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as RF amplifiers.

<sup>\*</sup> Indicates JEDEC Registered Data.



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### ELECTRICAL CHARACTERISTICS\* — continued (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS				•	
DC Current Gain (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	10	_	100	_
DYNAMIC CHARACTERISTICS				•	
Output Capacitance (V <sub>CB</sub> = 28 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	67	75	pF
BROADBAND FUNCTIONAL TESTS (Figure 6)					
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 60 W, f = 225–400 MHz)	G <sub>PE</sub>	7.8	8.5	_	dB
Electrical Ruggedness (Pout = 60 W, V <sub>CC</sub> = 28 Vdc, f = 400 MHz, VSWR 30:1 all phase angles)	Ψ	No Degradation in Output Power			_
NARROW BAND FUNCTIONAL TESTS (Figure 1)					
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 60 W, f = 400 MHz)	G <sub>PE</sub>	7.8	10	_	dB
Collector Efficiency (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 60 W, f = 400 MHz)	η	55	_	_	%

<sup>\*</sup> Indicates JEDEC Registered Data.

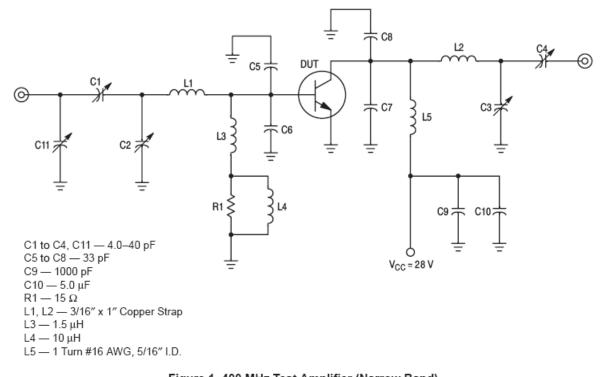


Figure 1. 400 MHz Test Amplifier (Narrow Band)

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f = 225 MHz

400 MHz

16

18 20

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#### NARROW BAND DATA

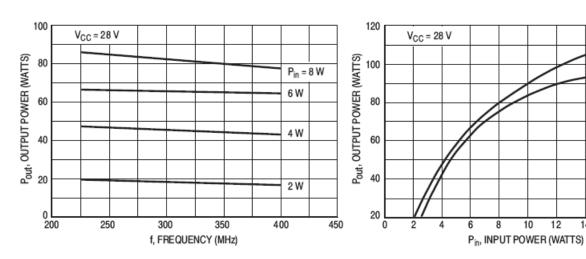


Figure 2. Pout versus Frequency

Figure 3. Output Power versus Input Power

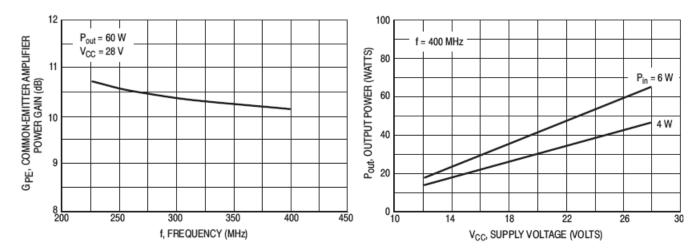


Figure 4. Power Gain versus Frequency

Figure 5. Output Power versus Supply Voltage

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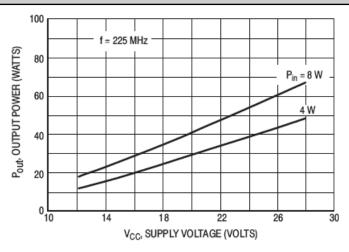
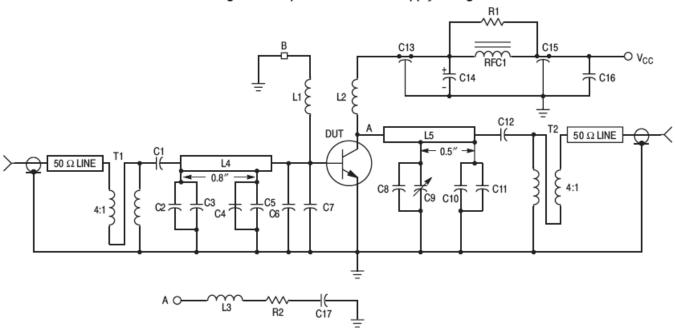


Figure 6. Output Power versus Supply Voltage



C1 — 68 pF C2, C4, C8, C10 - 27 pF C3, C5, C11 — 10 pF C6, C7 - 51 pF C9 - 1.0-10 pF JOHANSON C12 - 100 pF C13, C15 - 680 pF C14, C16 - 1.0 µF, 35 V Tantalum C17 - 0.1 µF, ERIE Red Cap

B — Ferroxcube 56-590-65/4B Ferrite Bead T1, T2 - 25 Ohms (UT25) Miniature Coaxial Cable, 1 turn R1 — 11 Ω, 1.0 W R2 - 20 Ω, 1/4 W

RFC1 — Ferrite Bead Choke, Feroxcube VK200 19/4B

L1 - 10 Turns, #22 AWG, 1/8" I.D.

L2 — 4 Turns, #16 AWG, 1/4" I.D.

L3 — 6 Turns, #24 AWG, 1/8" I.D. L4, L5 - 1" x 0.25" Microstrip Line

Board Material 0.031" Thick Teflon-Fiberglass

Figure 7. 225 to 400 MHz Broadband Test Circuit Schematic

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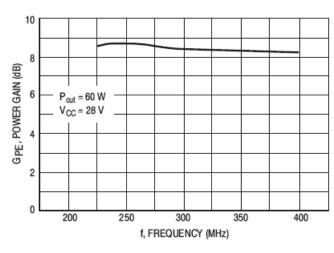
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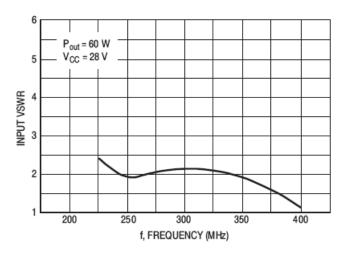
### **BROADBAND DATA (Circuit, Figure 7)**



100 Pout = 60 W VCC = 28 V 20 250 300 350 400 f, FREQUENCY (MHz)

Figure 8. Power Gain versus Frequency

Figure 9. Efficiency versus Frequency



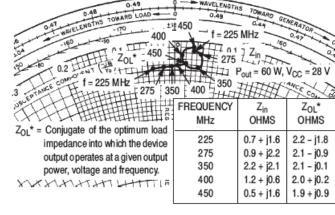


Figure 10. Input VSWR versus Frequency

Figure 11. Series Equivalent Input-Output Impedance

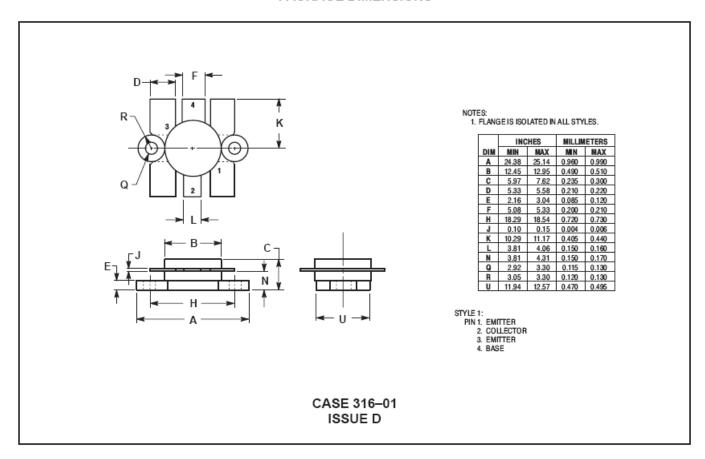
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#### PACKAGE DIMENSIONS



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